BTA212B series C

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope suitable for surface mounting intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

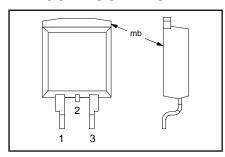
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BTA212B- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500C 500 12 95	600C 600 12 95	800C 800 12 95	V A A

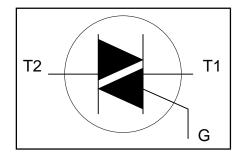
PINNING - SOT404

PIN	DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
mb	main terminal 2		

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
V_{DRM}	Repetitive peak off-state voltages			-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)}	RMS on-state current	full sine wave;	-		12		A
I _{TSM}	Non-repetitive peak on-state current	$T_{mb} \le 99 ^{\circ}\text{C}$ full sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge $t = 20 \text{ms}$			95		A
		t = 16.7 ms	-		105		
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after triggering	$ \begin{aligned} &t = 10 \text{ ms} \\ &I_{TM} = 20 \text{ A}; \ I_{G} = 0.2 \text{ A}; \\ &dI_{G}/dt = 0.2 \text{ A}/\mu\text{s} \end{aligned} $	-		45 100		A A ² s A/μs
I _{GM} V _{GM} P _{GM} P _{G(AV)}	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms			2 5 5 0.5		A V W W
T_{stg}	Storage temperature Operating junction temperature	ponou	-40 -		150 125		ပို့

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th i-a}	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	1 1 1	- - 60	1.5 2.0 -	K/W K/W K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
0.		T2+	+ G+	2	-	35	mΑ
		T2+	+ G-	2 2	-	35	mΑ
		T2-	· G-	2	-	35	mΑ
l _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
		T2+	+ G+	-	-	20	mΑ
		T2+	+ G-	-	-	30	mΑ
		T2-	· G-	-	-	20	mΑ
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	-	15	mΑ
V_{T}	On-state voltage	$I_{T} = 17 \text{ A}$		-	1.3	1.6	V
V _{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		-	0.7	1.5	V
	1	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_i = 125 ^{\circ}\text{C}$		0.25	0.4	-	V
I _D	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 °C$		-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

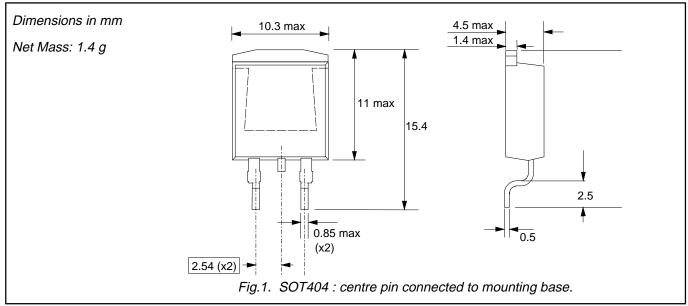
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	V _{DM} = 67% V _{DRM(max)} ; T _j = 125 °C; exponential waveform; gate open circuit	1000	-	V/μs
dI _{com} /dt	Critical rate of change of commutating current	V _{DM} = 400 V; T _j = 125 °C; I _{T(RMS)} = 12 A; without snubber; gate open circuit	3	14	A/ms
t _{gt}	Gate controlled turn-on time	$I_{TM} = 12 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $I_{G} = 0.1 \text{ A}$;	-	2	μs

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² Device does not trigger in the T2-, G+ quadrant.

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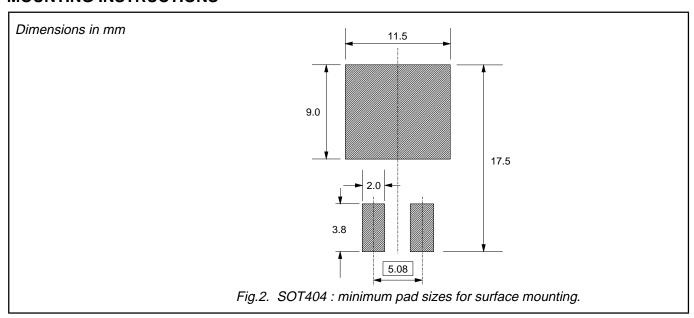
MECHANICAL DATA



Notes

1. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS



Notes

1. Plastic meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification This data sheet contains preliminary data; supplementary data may be publish					
Product specification This data sheet contains final product specifications.					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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